

Année	Auteurs	Titre		Signe	Conférence	Lieu, date	Actes
2011	N. Rodriguez, S. Cristoloveanu, F. Gamiz	New concepts for 1T-DRAMs: overcoming the scaling limits	Invited paper	CAS	34th Annual Semiconductor Conf.	Sinaia, Romania (17-21 oct. 2011)	Proc. in 34th CAS International Semiconductor Conference, Vol. 1, pp. 11-14 (2011)
2011	R. Hinchet, L. Montès, G. Bouteloup, G.A. Ardila Rodriguez, R. Parsa, H.-S. P. Wong, R. T. Howe	Electrical and Mechanical Characterization of NEMS switches		DTIP	Design, Test, Integration and Packaging of MEMS/MOEMS, IEEE Symposium	Aix-en-Provence, France (11-13 May 2011)	Proceedings of DTIP 2011, IEEE, pp. 348 - 351
2011	M. Charbonneau, J. Buckley, R. Tiron, M. Py, J. Barnes, N. Rochat, C. Licitra, G. Ghibaudo, and B. De Salvo,	NDR Controlled Multilevel Programming in PoRRAM with All-Organic Active Layer and Inert Electrodes.		ECS	219th Int ECS Symposium, Silicon Nitride, Silicon Dioxide, and Emerging Dielectrics	Montreal, Canada (May 2011).	Proc. ECS, pp. 2151-2043
2011	M. Bawedin, S. Cristoloveanu, S.J. Chang, M. Valenza, F. Martinez, J.H. Lee	Evaluation of interface trap density in advanced SOI MOSFETs		ECS	Symposium on Advanced Semiconductor on Insulator Technology and Related Physics	Montreal, Canada (1-6 mai 2011)	ECS Transactions, Vol. 35, no. 5, pp. 103-108 (2011)
2011	D. Bauza	Detailed analysis of Si-SiO ₂ interface traps in MOSFETs using charge pumping		ECS Spring Meeting	10th International Symposium on Silicon and Silicon Nitride and Silicon Dioxide Thin Insulating Films, 219rd meeting of the Electrochemical Society	Montréal, Canada, 1-6 mai 2011	ECS Transactions, Vol. 35, no.4, pp. 95-113, ISBN: 978-1-56677-865-7, doi: 10.1149/1.3572278 (2011)
2011	S.-J. Chang, M. Bawedin, W. Xiong, J.-H. Lee, S. Cristoloveanu	Hysteresis Effects in FinFETs with ONO Buried Insulator		ECS Spring Meeting	219th Electrochemical Society Meeting, Workshop on Advanced Semiconductor-on-Insulator Technology and Related Physics	Montréal, Canada, 1-6 mai 2011	ECS Transactions, Vol. 3, no. 5, pp. 79-84, doi:10.1149/1.3570780 (2011)
2011	N. Rodriguez, F. Gamiz, S. Cristoloveanu	New capacitorless dynamic memory compatible with SOI and bulk CMOS		ECS Spring Meeting	219th Meeting of the Electrochemical Society, Symposium on Advanced Semiconductor on Insulator Technology and Related Physics	Montreal, Canada (1-6 mai 2011)	ECS Transactions, Vol. 35, no. 5, pp. 195-200 (2011)
2011	S. Cristoloveanu	Novel SOI Structures and Characterization Strategy	Invited paper	ECS Spring Meeting	219th Electrochemical Society Meeting, Symposium on Advanced Semiconductor-on-Insulator Technology and Related Physics	Montréal, Canada (1-6 May 2012)	ECS Transactions, Vol. 35, no.5 pp. 93-102, doi:10.1149/1.3570782 (2011)

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2011	A. Ohata, Y-H. Bae, S. Cristoloveanu, C. Fenouillet-Beranger, P. Perreau, O. Faynot	Performance of SOI MOSFETs with ultra-thin body and buried-oxide		ECS Spring Meeting	219th Meeting of the Electrochemical Society, Symposium on Advanced Semiconductor on Insulator Technology and Related Physics	Montreal, Canada (1-6 May 2011)	ECS Transactions, Vol. 35, no. 5, pp. 247–252 (2011)
2011	G. Ghibaudo, J. Coignus, M. Charbonnier, J. Mitard, C. Leroux, X. Garros, R. Clerc, and G. Reimbold	Recent Findings in Electrical Behavior of CMOS High-K Dielectric/Metal Gate Stacks.	Invited paper	ECS Spring Meeting	11th International Symposium on Silicon Nitride, Silicon Dioxide, and Emerging Dielectrics, 219rd International Symposium of the Electrochemical Society	Montreal, Canada (May 2011)	ECS Transactions, Vol. 35, no.4, pp.773-804, ISBN:978-1-60768-215-8 , doi:10.1149/1.3572319 (2011)
2011	A. Diab, E. Saracco, I. Ionica, C. Bonafos, J.-F. Damlencourt, S. Cristoloveanu	Transport Properties of 3D Vertically Stacked SiGe and SiGeC Nanowires		ECS Spring Meeting	219th Electrochemical Society Meeting, Symposium on Advanced Semiconductor-on-Insulator Technology and Related Physics	Montréal, Canada, 1-6 mai 2013	ECS Transactions, Vol. 35, no.5, pp. 157-162, doi:10.1149/1.3570791 (2011)
2011	J.-L. Huguenin, J. Lacord, S. Monfray, R. Coquand, C. Baudot, T. Skotnicki, G. Ghibaudo and F. Boeuf	Comparative Study of Circuit Perspectives for Multi-Gate Structures at Sub-10nm Node		ESSDERC	ESSDERC 2011	Helsinki, Finland (sept 2011)	IEEE Conference proceedings, pp. 107-110
2011	C. Xu, P. Batude, K. Romanjek, C. Le Royer, C. Tabone, B.Previtali, M. A. Jaud, X Garros, M. Vinet, T. Poiroux (CEA/LETI), Q. Raffay, M. Mouis (IMEP-LAHC)	Improved extraction of GIDL in FDSOI devices for proper junction quality analysis		ESSDERC	41th European Solid-State Device Research Conference, ESSDERC	Helsinki, Finland (12-16 Sept. 2011)	IEEE Conference proceedings, pp. 267-270, doi:10.1109/ESSDERC.2011.6044183
2011	C. Diouf, A. Cros, S. Monfray, F. Boeuf, J. Rosa, J. Mitard, G. Ghibaudo	Transport Characterisation of Ge pMOSFETS in Saturation Regime		ESSDERC	ESSDERC 2011	Helsinki, Finland (sept 2011)	Proc. pp. 223 - 226
2011	R. Ritzenthaler, F. Lime, B. Nae, O. Faynot, S. Cristoloveanu, B. Iniquez	A short-channel analytical model for triple-gate and planar FDSOI transistors		Euro-SOI	7th Workshop of the Thematic Network on Silicon on Insulator technology, devices and circuits	Granada, Spain (17–19 janvier 2011)	Abstract booklet
2011	N. Rodriguez, F. Gamiz, S. Cristoloveanu	A2RAM: novel dual-body 1T-DRAM cell on ultrathin SOI		Euro-SOI	7th Workshop of the Thematic Network on Silicon on Insulator technology, devices and circuits	Granada, Spain (17–19 janvier 2011)	Abstract booklet

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2011	A. El Hajj Diab, I. Ionica, S. Cristoloveanu, F. Allibert, N. Rodriguez, F. Gamiz, M. Bawedin, Y.H. Bae, J. Chroboczek and G. Ghibaudo	Low-Frequency Noise in Ultrathin SOI Pseudo-MOSFET: Where is the Noise Coming From?		Euro-SOI	7th Workshop of the Thematic Network on Silicon on Insulator technology, devices and circuits	Granada, Spain (17-19 Jan. 2011)	Abstract booklet, pp. 23-24
2011	S-J. Chang, M. Bawedin, W. Xiong, J-H. Lee, S. Cristoloveanu	Scaling of SOI FinFlash memory with buried storage ONO layer		Euro-SOI	7th Workshop of the Thematic Network on Silicon on Insulator Technology, Devices and Circuits	Granada, Spain (17-19 janvier 2011)	Abstract booklet
2011	A. Cresti, S. Roche and P. Ordejón	Electronic transport in epoxide and methyl functionalized graphene nanoribbons	Poster	Graphene	Graphene 2011 – ImageNano	Bilbao, Spain, 11-14 April 2011	online at http://www.phantomsnet.net/imagenano/Abstracts/2011/Graphene2011_Cresti_Alessandro_crestial@minatec.inpg.fr_Abstract_Graphene2011.pdf
2011	R.L. Ribeiro, J.-M. Poumirol, A. Cresti, W. Escoffier, J.M. Broto, S. Roche and B. Raquet	Unveiling the Landau levels structure of graphene nanoribbons	Poster	Graphene	Graphene 2011 – ImageNano	Bilbao, Spain, 11-14 April 2011	online at http://www.phantomsnet.net/imagenano/Abstracts/2011/Graphene2011_Ribeiro_Rebeca_rebeca.ribeiro@lncmi.cnrs.fr_Abstract_Graphene2011_RIBEIRO.pdf
2011	F. Ortmann, A. Cresti, G. Montambaux and S. Roche	Weak localization vs. weak antilocalization in graphene		Graphene	Graphene 2011 – ImageNano	Bilbao, Spain, 11-14 April 2011	Imagenano 2011, p.93 - online at http://www.phantomsnet.net/imagenano/Abstracts/2011/Graphene2011_Ortmann_Frank_ortmann.f@googlemail.com_Imagenano2011_Abstract.pdf
2011	J. H. Choi, L. Latur-Romain, E. Bano	Fabrication of SiC nanopillars by inductively coupled SF6/O2 plasma		HeteroSiC-WASMPE	Joint "Workshop on SiC hetero-epitaxy" (HeteroSiC) and "Workshop on Advanced Semiconductor Materials and devices for Power Electronics applications" (WASPME)	Tours, France (27-30 June 2011)	Material Science Forum (à paraître)
2011	K Zekentes, K. Rogdakis, E. Bano	Material limitations for the development of high performance SiC NWFETs		HeteroSiC-WASMPE	Joint "Workshop on SiC hetero-epitaxy" (HeteroSiC) and "Workshop on Advanced Semiconductor Materials and devices for Power Electronics applications" (WASPME)	Tours, France (27-30 June 2011)	Material Science Forum (à paraître)

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2011	A. Zaka, D. Garetto, D. Rideau, P. Palestri, J. P. Manceau, E. Dornel, Q. Rafhay, R. Clerc, W. F. Clark, Y. Leblebici, C. Tavernier, and H. Jaouen	Characterization and modeling of gate current injection in embedded non-volatile flash memory		ICMTS	IEEE International Conference on Microelectronic Test Structures	Amsterdam, The Netherlands (4-7 April 2011)	Proceeding ISBN: 978-1-4244-8527-7
2011	A. Zaka, D. Garetto, R. Rideau, P. Palestri, J. Manceau, E. Dornel, Q. Rafhay, R. Clerc, Y. Leblebici, C. Tavernier, H. Jaouen	Characterization and modelling of gate current injection in embedded non-volatile flash memory		ICMTS	Microelectronic Test Structures (ICMTS), 2011 IEEE International Conference on	Amsterdam, The Netherlands (4-7 April 2011)	IEEE Conference proceedings
2011	Yong Xu, T. Minari, T. Kazuito, R. Gwoziecki, F. Balestra, J.A. Chroboczek, G. Ghibaudo	Analysis of Low Frequency Noise in Organic Field Effect Transistors Combining Static and Noise Data		ICNF	International Conference on Noise and Fluctuations (ICNF)	Toronto, June 2011	IEEE Conference Proceedings ICNF'2011, pp. 57-60, doi:10.1109/ICNF.2011.5994384 (2011)
2011	R. Jeyasingh, J.A.Chroboczek, Gérard Ghibaudo, Mireille Mouis, and H.-S. Philip Wong	Low Frequency Noise in Phase Change Materials		ICNF	International Conference on Noise and Fluctuations	Toronto, Canada (12-16 June 2011)	IEEE Conference Proceedings ICNF'2011, pp. 476-479, doi: 10.1109/ICNF.2011.5994373 (2011)
2011	S. Altazin, R. Clerc, R. Gwoziecki, D. Boudinet, G. Ghibaudo, G. Pananakakis, I. Chartier and R. Coppard	Characterisation and modelling of rectifying organic diode for RFID application		ICOE	International Conference on Organic Electronics 2011	Rome, Italy (22-24 June 2011)	Abstract booklet, O4.4 (1 page)
2011	Y. Xu, G. Ghibaudo, F. Balestra, M. Benwadih, R.Gwoziecki and R.Coppard	On the Temperature Dependence of Carrier Mobility in Organic Transistors.		ICOE	International Conference on Organic Electronics 2011	Rome, Italy (22-24 June 2011)	Abstract booklet, O1.2 (1 page)
2011	A. Castro-Carranza, M. Benwadin, R. Gwoziecki, Y. Xu, M. Estrada, A. Cerdeira, J. C. Nolasco, G. Ghibaudo, B. Iñiguez and J. Pallarès	Study of the dependence of mobility on the density of states in small molecule and polymeric OTFTs	Poster	ICOE	International Conference on Organic Electronics 2011	Rome, Italy (22-24 June 2011)	Abstract booklet, P2.3 (one page)
2011	F. Conzatti, M.G. Pala, D. Esseni, E. Bano, L. Selmi	A simulation study of strain induced performance enhancements in InAs nanowire Tunnel-FETs		IEDM	IEEE International Electron Devices Meeting	Washington, 5-7 Dec. 2011	IEEE Proceedings of IEDM, pp. 95-98

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2011	J. Mazurier, O. Weber, F. Andrieu, F. Allain, L. Tosti, L. Brévard, O. Rozeau, M.-A. Jaud, P. Perreau, C. Fenouillet-Beranger, F. A. Khaja, B. Colombeau, G. De Cock, G. Ghibaudo, M. Belleville, O. Faynot and T. Poiroux	Drain Current Variability and MOSFET Parameters Correlations in Planar FDSOI Technology		IEDM	IEEE International Electron Devices Meeting	Washington, 5-7 Dec. 2011	IEEE Proceedings of IEDM, pp. 575-578
2011	C. Cagni, J. Buckley, v. Jousseau, T. Cabout, A. Salaun, H. Grampeix, J. F. Nodin, H. Feldis, A. Persico, J. Cluzel, P. Lorenzi, L. Massari, R. Rao, F. Irrera, F. Aussenac, C. Carabasse, M. Coue, P. Calka, E. Martinez, L. Perniola, P. Blaise, Z.Fang, Y. H. Yu, G. Ghibaudo, D. Deleruyelle, M. Bocquet, C. Müller, A. Padovani, O. Pirrotta, L. Vandelli, L. Larcher, G. Reibold, B. de Salvo	Experimental and Theoretical Study of Electrode Effects in HfO2 based RRAM		IEDM	IEEE International Electron Devices Meeting	Washington, 5-7 Dec. 2011	IEEE Proceedings of IEDM, pp. 658-661
2011	E. G. Ioannidis, S. Haendler, A. Bajolet, T. Pahron, N. Planes, F. Arnaud, R.A.Bianchi, M.Haond, D.Golanski, J. Rosa, C. Fenouillet-Beranger, P. Perreau, C.A.Dimitriadis, G. Ghibaudo	Low frequency noise variability in high-k/metal gate stack 28nm bulk and FD-SOI CMOS transistors		IEDM	IEEE International Electron Devices Meeting	Washington, 5-7 Dec. 2011	IEEE Proceedings of IEDM, pp. 449-452

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2011	L. Masoero, G. Molas, F. Brun, M. Gély, J. P. Colonna, V. Della Marca, O. Cueto E. Nowak, A. De Luca, P. Brianceau, C. Charpin, R. Kies, A. Toffoli, D. Lafond, V. Delaye, F. Aussenac, C. Carabasse, S. Pauliac, C. Comboroure, G. Ghibaudo, S. Deleonibus, B. De Salvo	Optimization and scalability of split-gate charge trap memories down to 20nm for low-power embedded memories		IEDM	IEEE International Electron Devices Meeting	Washington, 5-7 Dec. 2011	IEEE Proceedings of IEDM, pp. 215-218
2011	I. Ionica, A. El Hajj Diab and S. Cristoloveanu	Gold nanoparticles detection using intrinsic SOI-based sensor		IEEE Nano	11th IEEE International Conference on Nanotechnology (IEEE Nano)	Portland, Oregon, USA, August 15-18, 2011	Proceedings of IEEE Nano 2011, IEEE, pp 38-43 (2011)
2011	L. Montès, R. Hinchet, X. Xu, A. Potié, J.W. Lee, G. Ardila, T. Baron, M. Mouis, R. Songmuang	NEMS Nanostructures with Enhanced Piezoresistive and Piezoelectric Properties: Application to Sensor Devices and Energy Harvesting		IEEE-NEMS	Annual International IEEE Conference on Nano/Micro Engineered and Molecular Systems, IEEE NEMS	Kaohsiung, Taiwan (20-23 Feb. 2011)	IEEE Conference Proceedings NEMS'2011, pp. 1064-1066, doi:10.1109/NEMS.2011.6017540 (2011)
2011	S.-J. Chang, M. Bawedin, W. Xiong, S.C. Jeon, J.-H. Lee, S. Cristoloveanu	A FinFET memory with remote carrier trapping in ONO buried insulator		INFOS	17th International Conf. Insulating Films on Semiconductors	Grenoble, France (21–24 June 2011)	INFOS 2011, (C. Leroux, G. Reimbold and S. Cristoloveanu eds.), Elsevier, pp. 1203–1206 (2011)
2011	K.-W. Kim, S.-D. Jung, D.-S. Kim, K.-S. Im, H.-S. Kang, J.-H. Lee, Y. Bae, D.-H. Kwon, S. Cristoloveanu	Charge trapping and interface characteristics in normally-off Al ₂ O ₃ /GaN-MOSFETs		INFOS	17th International Conf. Insulating Films on Semiconductors	Grenoble, France (21–24 June 2011)	Actes INFOS 2011 (C. Leroux, G. Reimbold and S. Cristoloveanu eds.), Elsevier, pp. 1225–1227 (2011)
2011	L. Masoero, P. Blaise, G. Molas, J. P. Colonna, M. Gély, J. P. Barnes, G. Ghibaudo, B. De Salvo,	Defects-induced gap states in hydrogenated γ -alumina used as blocking layer for NVM		INFOS	International Conference on Insulating Films on Semiconductors (INFOS)	Grenoble, France (21-24 juin 2011).	Extended papers in Microelectronic Engineering, Volume 88, Issue 7, July 2011, Pages 1315–1318
2011	T. Benoist, C. Fenouillet-Beranger, P. Perreau, C. Buj, P. Galy, D. Marin-Cudraz, O. Faynot, S. Cristoloveanu, P. Gentil	Experimental investigation of ESD design window for fully depleted SOI N-MOSFETs		INFOS	17th International Conf. Insulating Films on Semiconductors	Grenoble, France (21–24 June 2011)	INFOS 2011, (C. Leroux, G. Reimbold and S. Cristoloveanu eds.), Elsevier, pp. 1276–1279 (2011)

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2011	J. Wan, C. Le Royer, A. Zaskavsky, S. Cristoloveanu	Gate-induced drain leakage in FD-SOI devices: What the TFET teaches us about the MOSFET	INFOS	17th International Conf. Insulating Films on Semiconductors	Grenoble, France (21–24 juin 2011)	Proc. in INFOS 2011 (C. Leroux, G. Reimbold and S. Cristoloveanu eds.), Elsevier, pp. 1301–1304 (2011)
2011	T. Boutchacha and G. Ghibaudo,	Improved low frequency noise model for MOSFET operated in non-linear region.	INFOS	International Conference on Insulating Films on Semiconductors (INFOS)	Grenoble, France (21-24 juin 2011).	Extended papers in Microelectronic Engineering, Volume 88, Issue 7, July 2011, Pages 1280–1282
2011	M. A. Negara, D. Bauza, N. Goel, G. Ghibaudo, and P. K. Hurley	Interface state densities, low frequency noise and electron mobility in surface channel In _{0.53} Ga _{0.47} As n-MOSFETs with a ZrO ₂ gate dielectric	INFOS	International Conference on Insulating Films on Semiconductors (INFOS)	Grenoble, France (21-24 juin 2011).	Extended papers in Microelectronic Engineering, Volume 88 Issue 7, July, 2011, Pages 1095–1097
2011	A. El Hajj Diab, I. Ionica, S. Cristoloveanu, F. Allibert, Y. Bae, J. A. Chroboczek and G. Ghibaudo	Low-Frequency Noise in SOI Pseudo-MOSFET with Pressure Probes	INFOS	International Conference on Insulating Films on Semiconductors (INFOS)	Grenoble, France (21-24 juin 2011).	Proc. in INFOS 2011 (C. Leroux, G. Reimbold and S. Cristoloveanu eds.), Elsevier, pp. 1283–1285 (2011)
2011	D-S. Kim, T-H. Kim, C-H. Won, H-S. Kang, K-W. Kim, K-S. Im, Y-S. Lee, S-H. Hahm, J-H. Lee, J-H. Lee, J-B. Ha, Y. Bae, S. Cristoloveanu	Performance enhancement of GaN SB-MOSFET on Si substrate using two-step growth method	INFOS	17th International Conf. Insulating Films on Semiconductors	Grenoble, France (21-24 juin 2011)	INFOS 2011, (C. Leroux, G. Reimbold and S. Cristoloveanu eds.), Elsevier, pp. 1221–1224 (2011)
2011	A. Ohata, Y. Bae, T. Signamarcheix, J. Widiez, B. Ghyselen, O. Faynot, L. Clavelier, S. Cristoloveanu	Performance of (110) p-channel SOI-MOSFETs fabricated by deep-amorphization and solidphase epitaxial regrowth processes	INFOS	17th International Conf. Insulating Films on Semiconductors	Grenoble, France (21-24 juin 2011)	INFOS 2011, (C. Leroux, G. Reimbold and S. Cristoloveanu eds.), Elsevier, pp. 1265–1268 (2011)
2011	N. Rodriguez, S. Cristoloveanu, M. Maqueda, F. Gamiz, F. Allibert	Three-interface pseudo-MOSFET models for the characterization of SOI wafers with ultrathin film and BOX	INFOS	17th International Conf. Insulating Films on Semiconductors	Grenoble, France (21–24 juin 2011)	INFOS 2011, (C. Leroux, G. Reimbold and S. Cristoloveanu eds.), Elsevier, pp. 1236–1239 (2011)
2011	S. Baudot, C. Leroux, F. Chave, X. Garros, A. Toffoli, F. Allain, C. Gaumer, R. Boujamaa, E. Martinez, O. Renault, P. Caubet, O. Hinsinger, G. Reimbold, G. Ghibaudo, M. Silly, F. Sirotti	Understanding reversal effects of metallic Aluminum introduced in HfSiON/TiN PMOSFETs.	INFOS	International Conference on Insulating Films on Semiconductors (INFOS)	Grenoble, France (21-24 juin 2011).	Extended papers in Microelectronic Engineering, Volume 88, Issue 7, July 2011, Pages 1305–1308

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2011	L. Negre, D. Roy, S. Boret, P. Scheer, G. Ghibaudo	Advanced 45nm MOSFET Small-signal equivalent circuit aging under DC and RF hot carrier stress.		IRPS	IEEE International Reliability Physics Symposium	Monterey, CA, USA (april 2011)	Proc. pp. HV.1.1 - HV.1.4
2011	L. Negre, D. Roy, P. Scheer, D. Gloria, G. Ghibaudo	An Advanced RF-CV Method as a Powerful Characterization Tool for the Description of Hot Carriers Induced Defect Generation at Microscopic Level		IRW	IEEE IRW	Stanford Sierra, USA (Oct 2011)	Abstract D7,2
2011	L. Negre, D. Roy, P. Scheer, D. Gloria, G. Ghibaudo	An advanced RF-CV method as a powerful characterization tool for the description of HC induced defect generation at microscopic level		IRW	IEEE Integrated Reliability Workshop (IRW'2011)		IEEE IRW Final Report, ISBN: 978-1-4577-0115-3, pp. 73-76 (2011)
2011	D. Bauza	Charge pumping: an overview of the technique and recent new features	Invited Lecture	IRW	IEEE Integrated Reliability Workshop	Stanford Sierra Camp Conf. Center, Fallen Leaf Lake, CA, USA (16-20 October 2011)	Non encore publiés
2011	A. Diab, I. Ionica, S. Cristoloveanu, F. Allibert, Y.H. Bae, J.A. Chroboczek and G. Ghibaudo	Static and Low-Frequency Noise Characterization of Ultrathin SOI with Very Thin BOX in Pseudo-MOSFET Configuration		ISDRS	International Semiconductor Device Research Symposium	College Park, Maryland, USA (7-9 Dec. 2011)	Conference Proceedings TP4.02
2011	P. Febvre, R. Collot, N. De Leo, M. Fretto, A. Sosso, V. Lacquaniti	Overdamped Josephson junctions for digital applications	Invited paper	ISS	24th International Symposium on Superconductivity (ISS 2011)	Tokyo, Japan - October 24-26, 2011	Proceedings of ISS2011
2011	L. Montès, X. Xu, A. Potié, B. Bercu, J. Lee, D. Jang, GT Kim, G. Ardila, P. Morfouli, M. Mouis, T. Baron, B. Salem, R. Sonamuang	Nanowire devices: Enhancing piezoresistivity and piezoelectricity	Invited paper	NEMS	IEEE International Conference on Nano/Micro Engineered and Molecular Systems	CGU Taiwan, June 21 2011	Proceedings of NEMS 2011, IEEE, pp. 1064 - 1066
2011	L. Negre, D. Roy, F. Cacho, P. Scheer, S. Boret, A. Zaka, D. Gloria, G. Ghibaudo	Aging of 40-nm MOSFET RF Parameters under RF conditions From characterization to Compact Modeling for RF design		RFIC	Int Conf IEEE RFIC 2011	Baltimore, USA (June 2011).	Proc. IEEE, pp. 1-4

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2011	J. R. Ngankio-Njila, D-G. Crété, J-C. Mage, B. Marcilhac and P. Febvre	Progress on superconducting comparators for pipe-line A/D conversion		SCC	Superconductivity Centennial Conference (SCC-2011)	The Hague, The Netherlands, 18-23 September 2011	
2011	Th. Wolf, N. Bergeal, J. Lesueur, C.J. Fourie, G. Faini, C. Ulysse and P. Febvre	Study of YBCO strip-line inductances connected to nano-Josephson junctions		SCC	Superconductivity Centennial Conference (SCC-2011)	The Hague, The Netherlands, 18-23 September 2011	
2011	M. A. Negara, K. Cherkaoui, C. D. Young, P. Majhi, W. Tsai, D. Bauza, G. Ghibaudo, and P. K. Hurley	Analysis of Electron Mobility in HfO ₂ /TiN Gate MOSFETs: The Influence of HfO ₂ Thickness, Temperature and Oxide Charge		SISC	IEEE Semiconductor Interface Specialists Conference	San Diego, USA (Dec 2011)	Sans - mais très sélectif
2011	S. Baudot, C. Leroux, F. Chave, P. Caubet, G. Reimbold, G. Ghibaudo	Modulation of High-K/Metal Gate Effective Work Function and its Roll-Off by Lanthanum addition		SISC	IEEE Semiconductor Interface Specialists Conference	San Diego, USA (Dec 2011)	Sans - mais très sélectif
2011	F. Palumbo, E. Miranda, G. Ghibaudo and V. Jousseume	Model and Fitting Results for the Filamentary Conduction in MIM Resistive Switching Devices		SMTD	26th Symposium on Microelectronics Technology and Devices	Joao Pessoa, Brazil (Aug 2011).	ECS Transactions 39, 187 (2011)
2011	S.J. Chang, M. Bawedin, B. Bayraktaroglu, J.H. Lee, S. Cristoloveanu	Low-Temperature Properties of ZnO on Insulator MOSFETs		SOI Conf	2011 IEEE International SOI Conference	Tempe, Arizona, USA (3-6 oct. 2011)	IEEE Conference Proceedings, pp. XX, ISBN: 978-1-61284-759-7
2011	N. Rodriguez, F. Andrieu, C. Navarro, O. Faynot, F. Gamiz, S. Cristoloveanu	Properties of 22 nm node extremely-thin-SOI MOSFETs		SOI Conf	2011 IEEE Int. SOI Conf.	Tempe, Arizona, USA (3-6 oct. 2011)	IEEE Conference Proceedings, ISBN: 978-1-61284-759-7, 2 pages, doi: 10.1109/SOI.2011.6081681
2011	N. Rodriguez, C. Navarro, F. Andrieu, O. Faynot, F. Gamiz, S. Cristoloveanu	Self-heating effects in ultrathin SOI MOSFETs		SOI Conf	2011 IEEE Int. SOI Conf.	Tempe, Arizona, USA (3-6 oct. 2011)	IEEE Conference Proceedings, ISBN: 978-1-61284-759-7, 2 pages, doi: 10.1109/SOI.2011.6081685
2011	J. Lacord, D. Hoguet, D. Rideau, G. Ghibaudo, and F. Boeuf	Accurate and ready-to-use Parasitics Capacitance Models for Advanced 2D/3D CMOS Device Structure Comparison		SSDM	International Conference on Solid State Devices and Materials (SSDM)	Nagoya, Japan (28-30 Sept. 2011)	Proc. pp. D1,1-D1,4
2011	J. Lacord, J.-L. Huguenin, G. Ghibaudo, T. Skotnicki and F. Boeuf,	Simple and Efficient MASTAR Threshold Voltage and Subthreshold Slope Models for Double Gate Structures		SSDM	International Conference on Solid State Devices and Materials (SSDM)	Nagoya, Japan (28-30 Sept. 2011)	Proc. pp. D3,1-3,4

Année	Auteurs	Titre		Sigle	Conférence	Lieu, date	Actes
2011	I. Ben Akkez, A. Cros, C. Fenouillet-Beranger, P. Perreau, A. Margain, F. Bœuf, F. Balestra, G. Ghibaudo	Characterization and Modeling of Capacitances in FD-SOI Devices		ULIS	Int. Conference on Ultimate Integration of Silicon	Cork, Ireland (14-16 March 2011)	IEEE Conference Proceedings, doi:10.1109/ULIS.2011.5757984, 4 pages (March 2011)
2011	M. Clavel, T. Poiroux, M. Mouis, L. Becerra, J.L Thomassin, A. Zenasni, G. Lapertot, D. Rouchon, D. Lafond and O. Faynot	Influence of annealing temperature on the performance of Graphene / SiC transistors with high-k / metal gate		ULIS	Int. Conference on Ultimate Integration of Silicon	Cork, Ireland (14-16 March 2011)	IEEE Conference Proceedings, pp. 171-174, doi:10.1109/ULIS.2011.5757955 (March 2011)
2011	Q. Rafhay, Cuiqin Xu, P. Batude, M. Mouis, M. Vinet and G. Ghibaudo	Revisited approach for the characterization of Gate Induced Drain Leakage		ULIS	Int. Conference on Ultimate Integration of Silicon	Cork, Ireland (14-16 March 2011)	IEEE Conference Proceedings, pp. 179-182, doi:10.1109/ULIS.2011.5757994 (March 2011)
2011	A. Zaslavsky, J. Wan, S.T. Le, P. Jannaty, S.A. Dayeh, C. Le Royer, S. Cristoloveanu, S.T. Picraux	Abrupt switching devices : from tunneling to positive feedback	Invited paper	WOFE	International Advanced Workshop on 'Frontiers in Electronics' (WOFE'11)	San Juan, Puerto Rico (18-21 Dec. 2011)	Sans
2011	F. Gamiz, N. Rodriguez, S. Cristoloveanu	Advanced concepts for floating-body memories	Invited paper	WOFE	International Advanced Workshop on 'Frontiers in Electronics' (WOFE'11)	San Juan, Puerto Rico (18-21 Dec. 2011)	Sans
2011	S.-J. Chang, M. Cheralathan, M. Bawedin, B. Iniguez, B. Bayraktaroglu, J-H. Lee, S. Cristoloveanu	Mobility behaviour and models for ZnO TFTs		WOFE	International Advanced Workshop on 'Frontiers in Electronics' (WOFE'11)	San Juan, Puerto Rico (18-21 Dec. 2011)	Sans
2011	K.-S. Im, K.-W. Kim, D.-S. Kim, H.-S. Kang, S.-D. Jung, C.-H. Bu, C.-H. Won, R.-H. Kim, K.-I. Jang, M.-K. Kwon, J.-H. Lee, S.-J. Chang, S. Cristoloveanu	Normally-off operation of GaN-based FinFET		WOFE	International Advanced Workshop on 'Frontiers in Electronics' (WOFE'11)	San Juan, Puerto Rico (18-21 Dec. 2011)	Sans